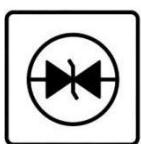




ESD



TVS



TSS



MOV



GDT



PLED

MSESD8D3.3CAT5G

Product specification

Features

- 60Watts peak pulse power ($t_p = 8/20\mu s$)
- Tiny DFN1006 package
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- IEC 61000-4-2 $\pm 15kV$ contact $\pm 20kV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 6A (8/20 μs)

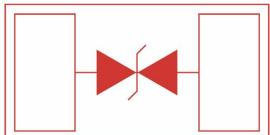
Applications

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation

Mechanical Data

- DFN1006 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Reference News

PACKAGE OUTLINE	SCHEMATIC & PIN CONFIGURATION	MARKING
 DFN1006		

Absolute Maximum Rating

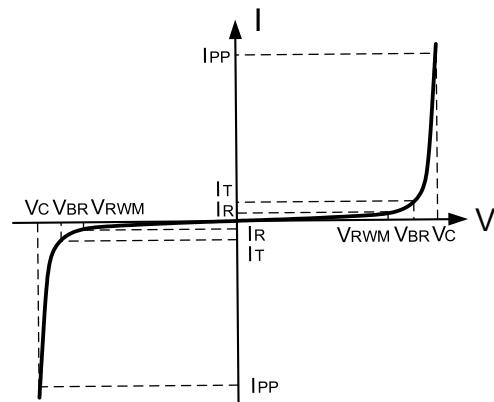
Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20\mu s$)	P_{pp}	60	Watts
Peak Pulse Current ($t_p = 8/20\mu s$) (note1)	I_{pp}	6	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	20 15	kV
Lead Soldering Temperature	T_L	260(10seconds)	°C
Junction Temperature	T_J	-55 to + 125	°C
Storage Temperature	T_{stg}	-55 to + 125	°C

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				3.3	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$	3.8			V
Reverse Leakage Current	I_R	$V_{RWM} = 3.3\text{V}, T = 25^\circ\text{C}$			0.5	μA
Clamping Voltage ²⁾	V_C	$I_{PP} = 6\text{A}, t_p = 8/20\mu\text{s}$		8		V
Junction Capacitance	C_J	$V_R = 0\text{V}, f = 1\text{MHz}$		12		pF

Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current



Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

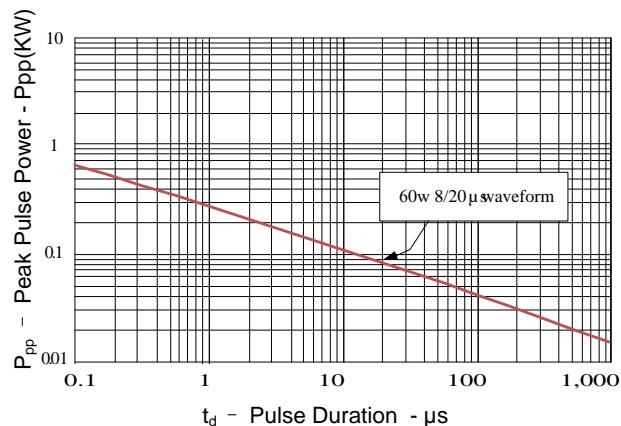


Figure 2: Power Derating Curve

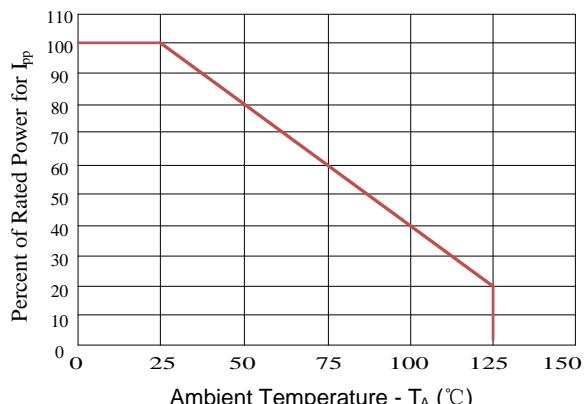


Figure3: Pulse Waveform

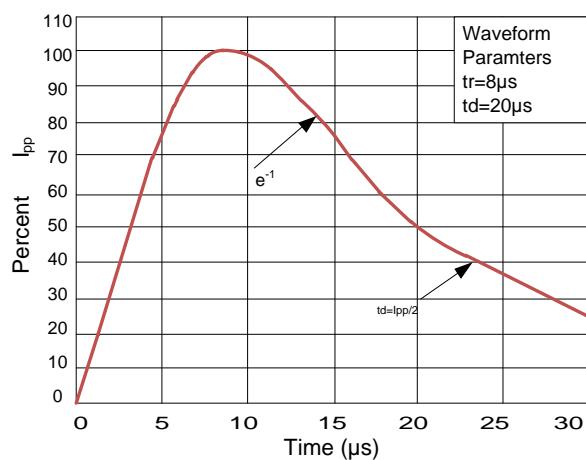
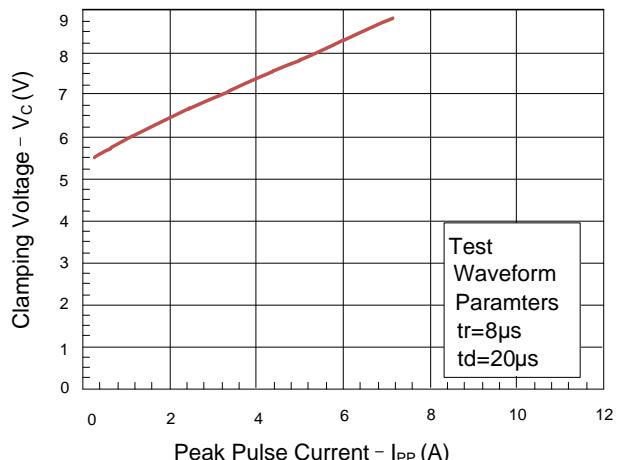
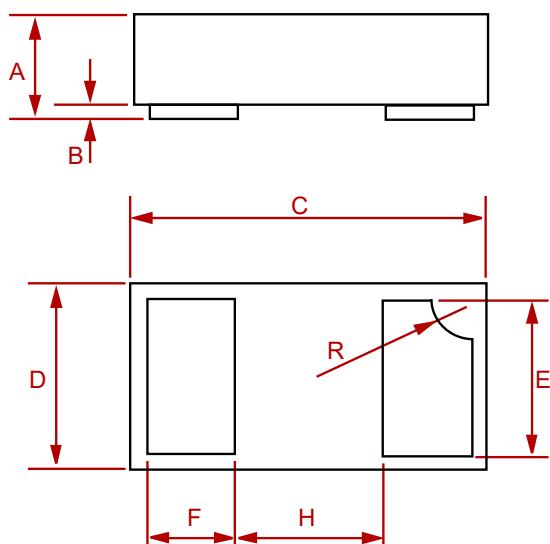
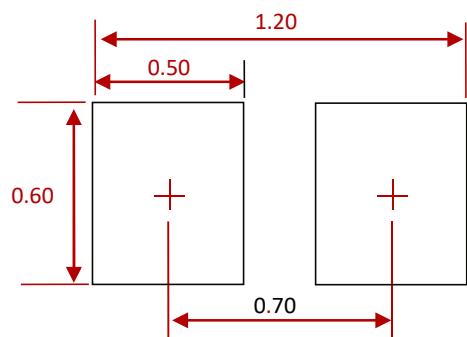


Figure 4: Clamping Voltage vs.Ipp



PACKAGEMECHANICALDATA


Dim	Inches		Millimeters	
	MIN	MAX	MIN	MAX
A	0.0125	0.02	0.32	0.52
B	0.000	0.002	0.00	0.05
C	0.037	0.043	0.95	1.080
D	0.022	0.027	0.55	0.680
E	0.016	0.024	0.40	0.60
F	0.008	0.012	0.20	0.30
H	0.015Typ.		0.40Typ.	
R	0.001	0.005	0.05	0.15

Suggested Pad Layout

NOTES:

1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY.
CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR
COMPANY'S MANUFACTURING GUIDELINES ARE MET.

REELSPECIFICATION

P/N	PKG	QTY
MSESD8D3.3CAT5G	DFN1006	10000

Attention

- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- MSKSEMI Semiconductor strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the MSKSEMI Semiconductor product that you intend to use.